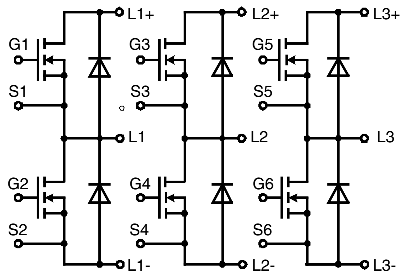
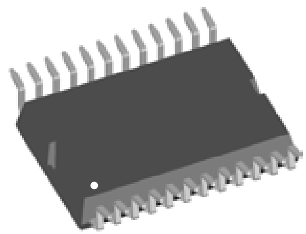
Three phase full Bridge

with Trench MOSFETs
in DCB isolated high current package

V_{DSS} = 40 V
I_{D25} = 180 A
$R_{DSon\ typ.}$ = 1.9 mΩ

Preliminary data





MOSFETs

Symbol	Conditions	Maximum Ratings	
V_{DSS}	T_{VJ} = 25°C to 150°C	40	V
V_{GS}		± 20	V
I_{D25} I_{D90} I_{D110}	T_C = 25°C T_C = 90°C T_C = 110°C	180 136 120	A A A
I_{F25} I_{F90} I_{F110}	T_C = 25°C (diode) T_C = 90°C (diode) T_C = 110°C (diode)	182 112 88	A A A

Symbol	Conditions		Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
R_{DSon} [1)]	on chip level at V_{GS} = 10 V	T_{VJ} = 25°C T_{VJ} = 125°C		1.9 2.8	2.5 5.3	mΩ mΩ
$V_{GS(th)}$	V_{DS} = 20 V; I_D = 1 mA		2.5		4.5	V
I_{DSS}	$V_{DS} = V_{DSS}$; V_{GS} = 0 V	T_{VJ} = 25°C T_{VJ} = 125°C		 50	5	μA μA
I_{GSS}	V_{GS} = ± 20 V; V_{DS} = 0 V				0.2	μA
Q_g Q_{gs} Q_{gd}	V_{GS} = 10 V; V_{DS} = 20 V; I_D = 100 A			110 33 30		nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off} E_{recoff}	inductive load V_{GS} = +10/0 V; V_{DS} = 15 V I_D = 135 A; R_G = 39 Ω; T_J = 125°C			150 240 350 170 0.12 0.51 0.003		ns ns ns ns mJ mJ mJ
R_{thJC} R_{thJH}	 with heat transfer paste (IXYS test setup)			 1.3	1.0 1.6	K/W K/W

1) $V_{DS} = I_D \cdot (R_{DS(on)} + R_{Pin\ to\ Chip})$

Applications

AC drives
- in automobiles
  - electric power steering
  - starter generator
- in industrial vehicles
  - propulsion drives
  - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
  - low R_{DSon}
  - optimized intrinsic reverse diode
- package:
  - high level of integration
  - high current capability
  - aux. terminals for MOSFET control
  - terminals for soldering or welding connections
  - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

IXYS reserves the right to change limits, test conditions and dimensions.
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Recommended replacement: MTI150WX40GD

Source-Drain Diode					
Symbol	**Conditions**	**Characteristic Values** (T_J = 25°C, unless otherwise specified)			
		min.	**typ.**	**max.**	
V_{SD}	(diode) I_F = 100 A; V_{GS} = 0 V		0.9	1.2	V
t_{rr}	I_F = 100 A; $-di_F/dt$ = 600 A/µs V_R = 15 V; T_J = 125°C		38		ns
Q_{RM}			0.31		µC
I_{RM}			14		A

Component			
Symbol	**Conditions**	**Maximum Ratings**	
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections 2 pins for output L1, L2, L3	75	A
T_J		-55...+175	°C
T_{stg}		-55...+125	°C
V_{ISOL}	I_{ISOL} ≤ 1 mA, 50/60 Hz, f = 1 minute	1000	V~
F_C	mounting force with clip	50 - 250	N

Symbol	**Conditions**	**Characteristic Values**			
		min.	**typ.**	**max.**	
$R_{pin\ to\ chip}$ [1)]	L+ to L1/L2/L3 or L- to L1/L2/L3		0.9		mΩ
C_P	coupling capacity between shorted pins and back side metallization		160		pF
Weight			25		g

1) $V_{DS} = I_D \cdot (R_{DS(on)} + R_{Pin\ to\ Chip})$

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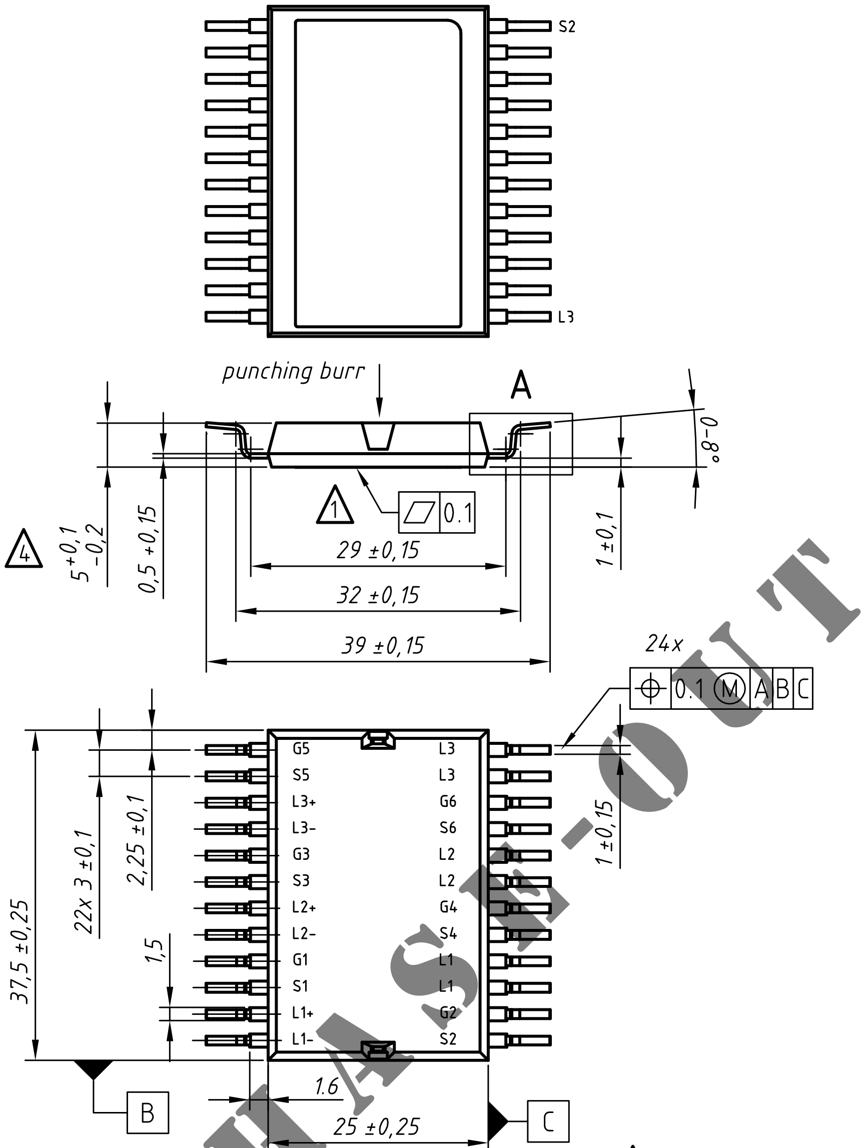
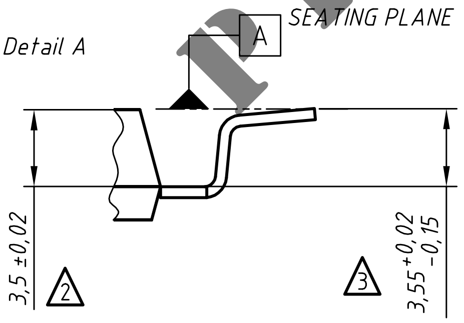


Detail A



1. Convex bow of substrate, typ. 10-40 µm longitudinal and 5-15 µm transversal
2. Distance between pin and case bottom side.
3. Distance between pin and contact surface.
4. Distance between parallel planes aligned to top and bottom sides of the package

contact pin:
- galv. tin plating, per pin side: Sn 10...25 µm, undercoating Ni 0,2...1 µm
- stamping edges may be free of tin
- puching burr: ≤ 0,05mm

Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
SMD	Standard	GMM 3x180-004X2 - SMD	GMM 3x180-004X2	Blister	28	509042

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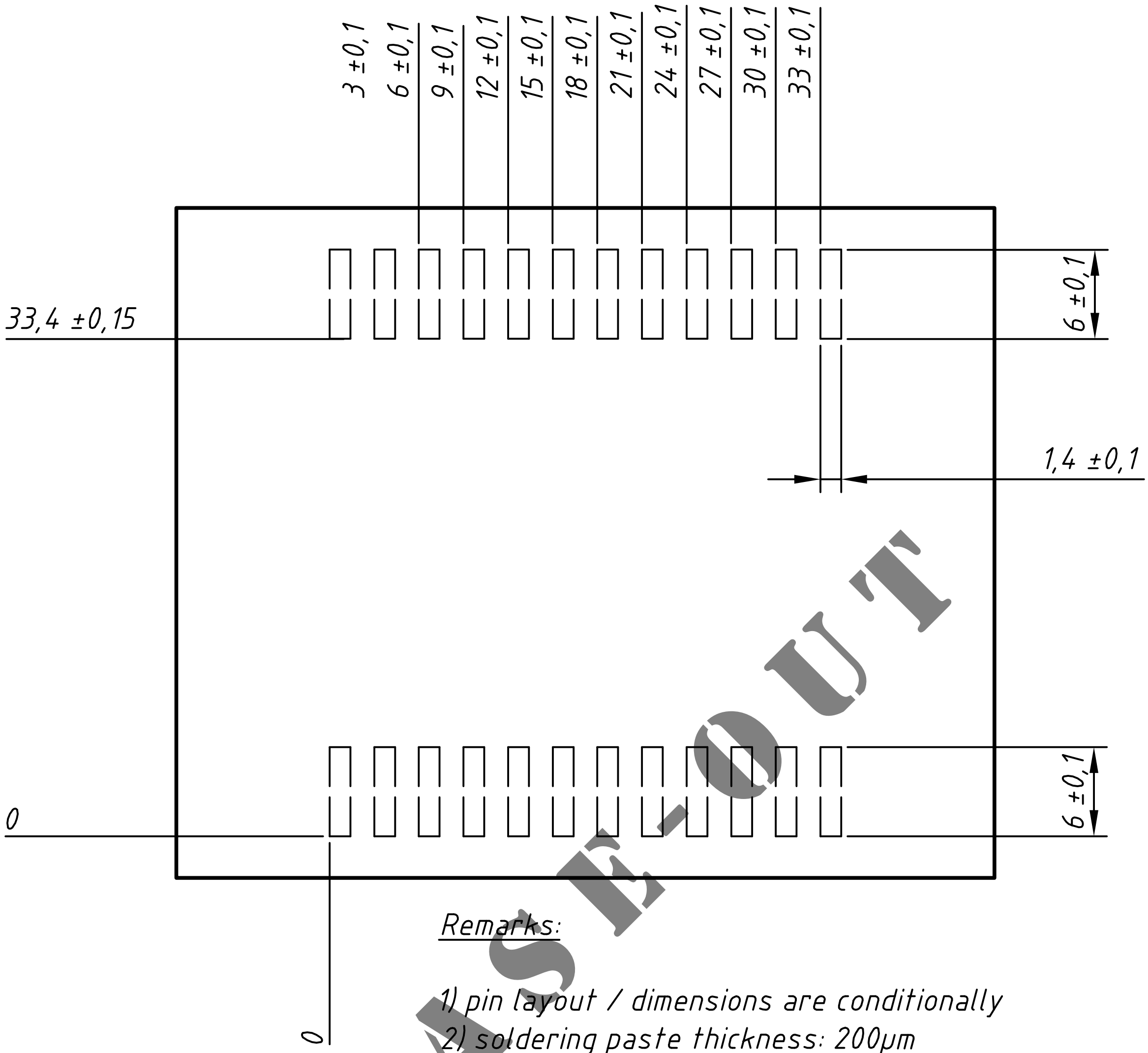

Remarks:

1) pin layout / dimensions are conditionally
2) soldering paste thickness: 200µm

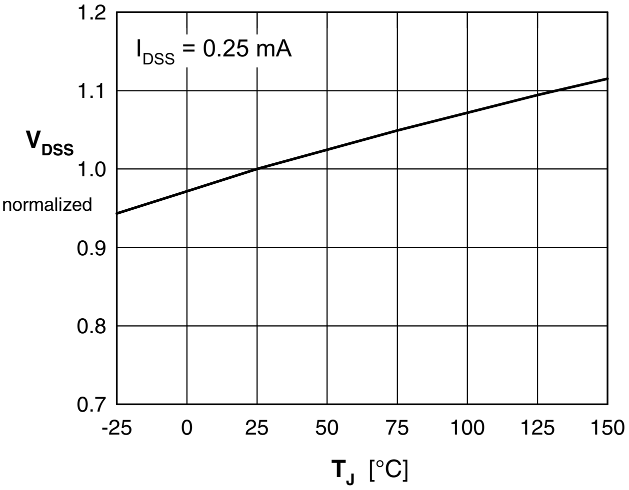

Fig. 1 Drain source breakdown voltage V_{DSS} vs. junction temperature T_{VJ}

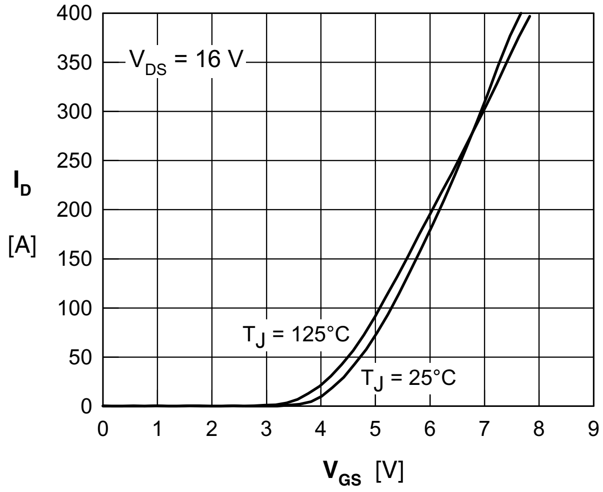

Fig. 2 Typical transfer characteristic

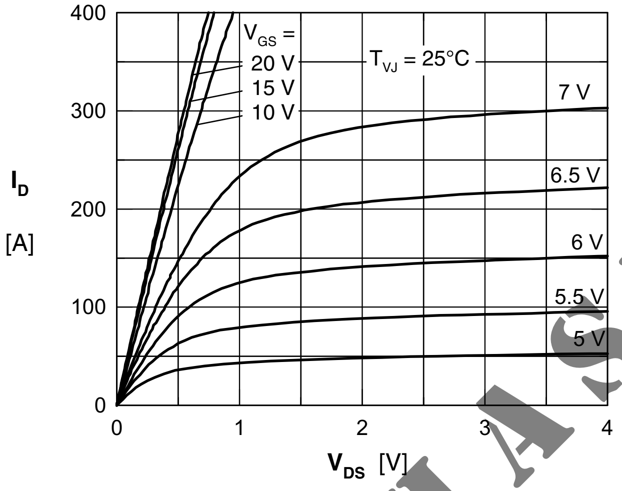

Fig. 3 Typical output characteristic

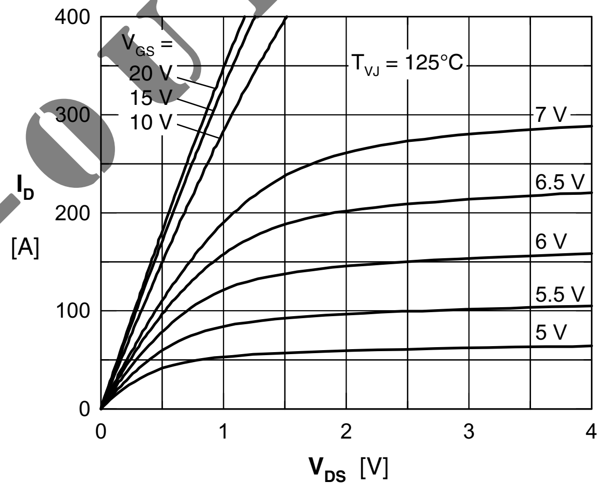

Fig. 4 Typical output characteristic

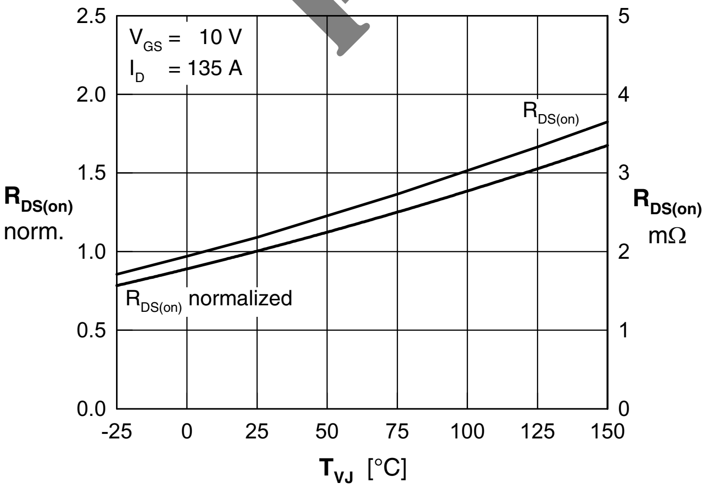

Fig. 5 Typ. drain source on-state resistance $R_{DS(on)}$ versus junction temperature T_J

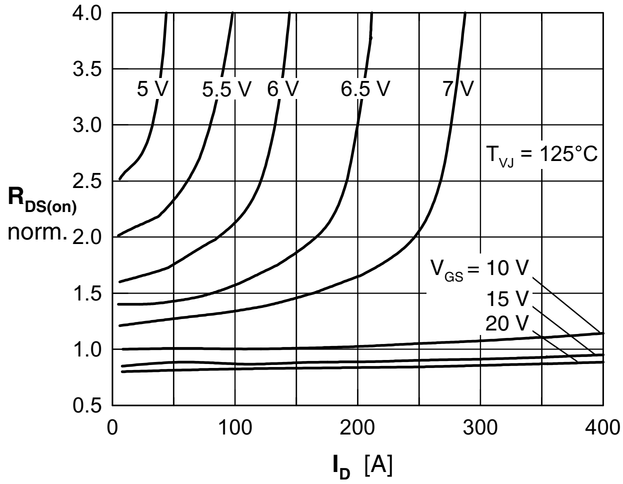

Fig. 6 Typ. drain source on-state resistance $R_{DS(on)}$ versus I_D

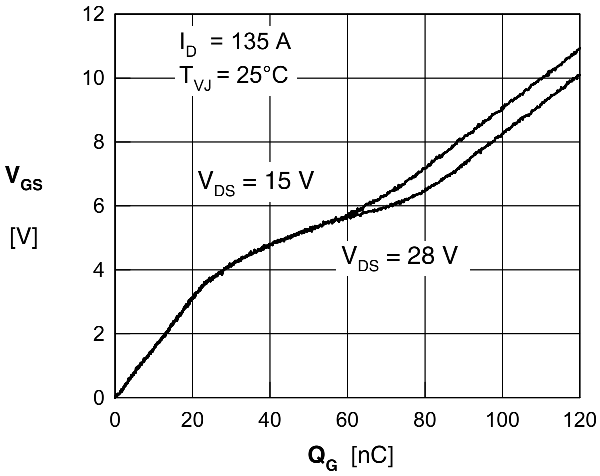

Fig. 7 Gate charge characteristics

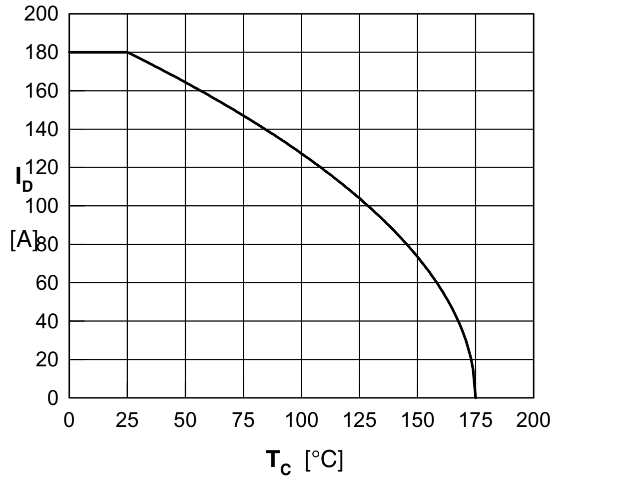

Fig. 8 Drain current I_D vs. temperature T_C

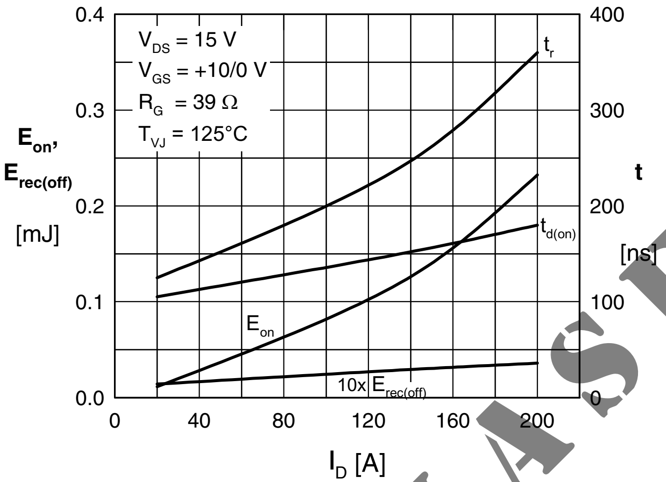

Fig. 9 Typ. turn-on energy & switching times vs. collector current, inductive switching

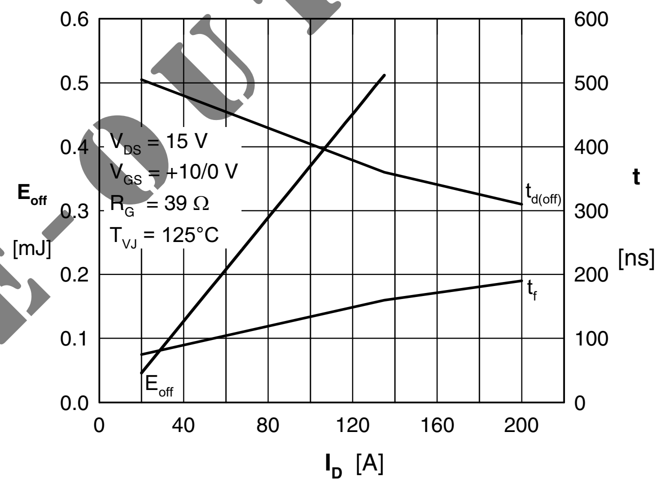

Fig. 10 Typ. turn-off energy & switching times vs. collector current, inductive switching

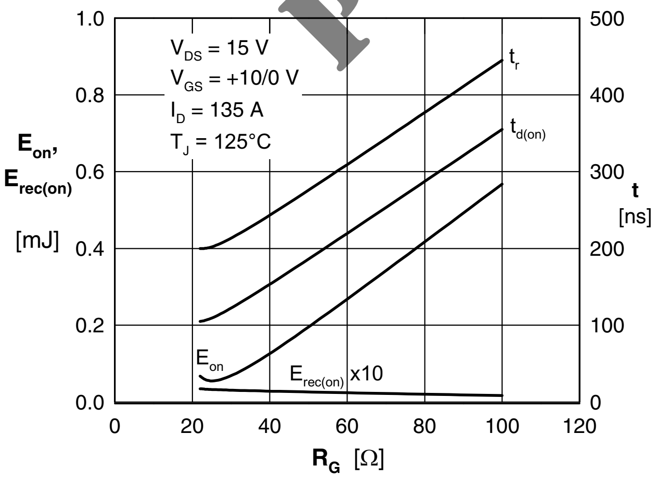

Fig. 11 Typ. turn-on energy & switching times vs. gate resistor, inductive switching

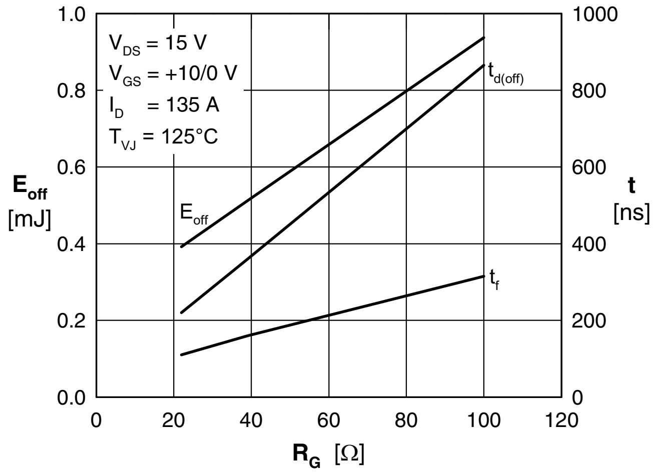

Fig. 12 Typ. turn-off energy & switching times vs. gate resistor, inductive switching

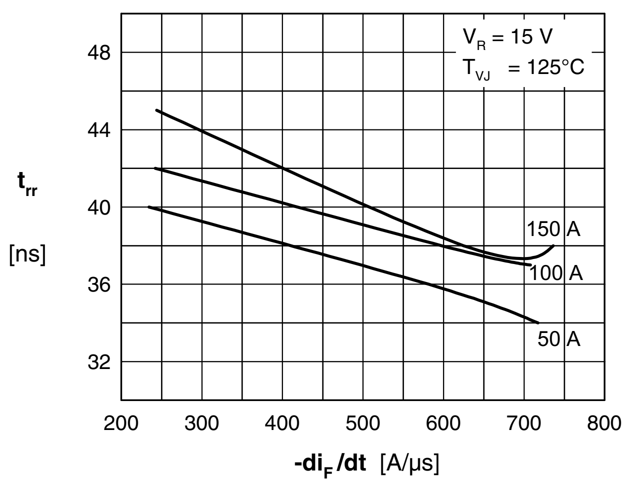

Fig. 13 Typ. reverse recovery time t_{rr} of the body diodes versus di/dt

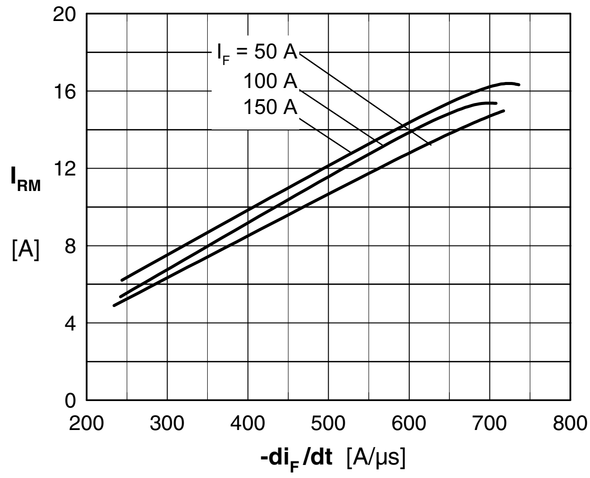

Fig. 14 Typ. reverse recovery current I_{RM} of the body diodes versus di/dt

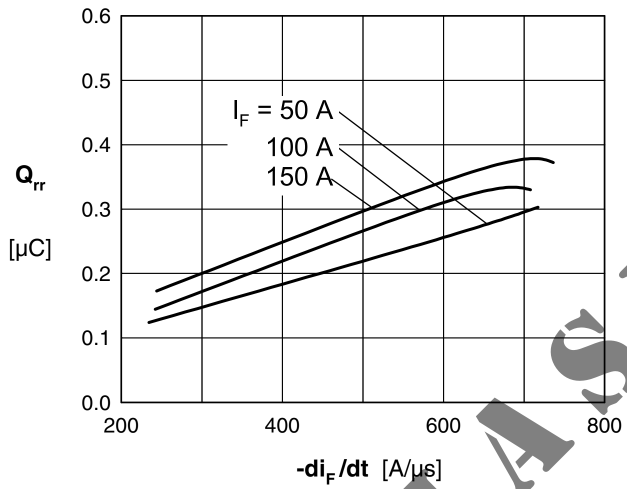

Fig. 15 Typ. reverse recovery charge Q_{rr} of the body diodes versus di/dt

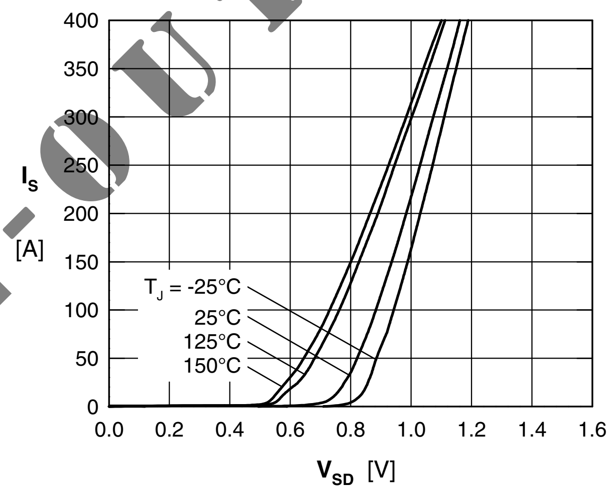

Fig. 16 Typ. source current I_S versus source drain voltage V_{SD} (body diode)

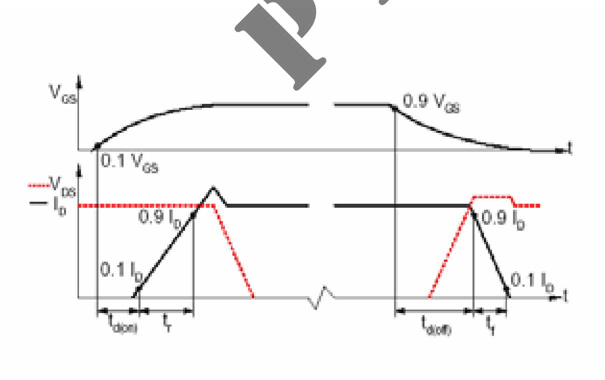

Fig. 17 Definition of switching times